www.ti.com

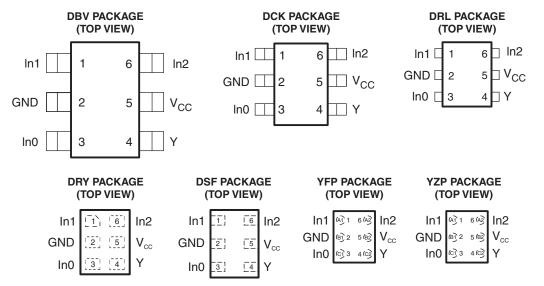
LOW-POWER CONFIGURABLE MULTIPLE-FUNCTION GATE

Check for Samples: SN74AUP1G58

FEATURES

- Available in the Texas Instruments NanoStar™ Packages
- Low Static-Power Consumption (I_{CC} = 0.9 μA Max)
- Low Dynamic-Power Consumption (C_{pd} = 4.6 pF Typ at 3.3 V)
- Low Input Capacitance (C_i = 1.5 pF Typ)
- Low Noise Overshoot and Undershoot <10% of V_{CC}
- I_{off} Supports Partial-Power-Down Mode Operation
- Includes Schmitt-Trigger Inputs

- Wide Operating V_{CC} Range of 0.8 V to 3.6 V
- Optimized for 3.3-V Operation
- 3.6-V I/O Tolerant to Support Mixed-Mode Signal Operation
- $t_{nd} = 5.5 \text{ ns Max at } 3.3 \text{ V}$
- Suitable for Point-to-Point Applications
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22
 - 2000-V Human-Body Model (A114-B, Class II)
 - 1000-V Charged-Device Model (C101)



See mechanical drawings for dimensions.

DESCRIPTION/ORDERING INFORMATION

The AUP family is TI's premier solution to the industry's low-power needs in battery-powered portable applications. This family ensures a very low static and dynamic power consumption across the entire V_{CC} range of 0.8 V to 3.6 V, resulting in an increased battery life. This product also maintains excellent signal integrity, which produces very low undershoot and overshoot characteristics.

The SN74AUP1G58 features configurable multiple functions. The output state is determined by eight patterns of 3-bit input. The user can choose the logic functions AND, OR, NAND, NOR, XNOR, inverter, and noninverter. All inputs can be connected to V_{CC} or GND.

The device functions as an independent gate with Schmitt-trigger inputs, which allow for slow input transition and better switching noise immunity at the input.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



NanoStar™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

ORDERING INFORMATION⁽¹⁾

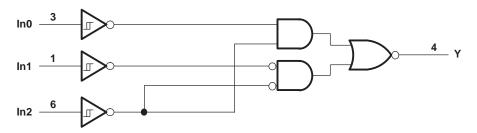
T _A	PACKAGE ⁽²⁾		ORDERABLE PART NUMBER	TOP-SIDE MARKING ⁽³⁾
	NanoStar™ – WCSP (DSBGA) 0.23-mm Large Bump – YFP (Pb-free)	Reel of 3000	SN74AUP1G58YFPR	HJ_
	NanoStar™ – WCSP (DSBGA) 0.23-mm Large Bump – YZP (Pb-free)	Reel of 3000	SN74AUP1G58YZPR	HJ_
-40°C to 85°C	QFN – DRY	Reel of 5000	SN74AUP1G58DRYR	HJ
	uQFN – DSF	Reel of 5000	SN74AUP1G58DSFR	HJ
	SOT (SOT-23) – DBV	Reel of 3000	SN74AUP1G58DBVR	H58_
	SOT (SC-70) – DCK	Reel of 3000	SN74AUP1G58DCKR	HJ_
	SOT (SOT-553) – DRL	Reel of 4000	SN74AUP1G58DRLR	HJ_

- (1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.
- (2) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.
- (3) DBV/DCK/DRL: The actual top-side marking has one additional character that designates the wafer fab/assembly site. YFP/YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the wafer fab/assembly site. Pin 1 identifier indicates solder-bump composition (1 = SnPb, = Pb-free).

FUNCTION TABLE

	INPUTS		OUTPUT
ln2	ln1	In0	Υ
L	L	L	L
L	L	Н	Н
L	Н	L	L
L	Н	Н	Н
Н	L	L	Н
Н	L	Н	Н
Н	Н	L	L
Н	Н	Н	L

LOGIC DIAGRAM (POSITIVE LOGIC)



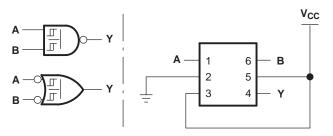
Submit Documentation Feedback



FUNCTION SELECTION TABLE

LOGIC FUNCTION	FIGURE NO.
2-input AND with inverted input	2, 3
2-input NAND	1
2-input NAND with both inputs inverted	4
2-input OR	4
2-input OR with both inputs inverted	1
2-input NOR with inverted input	2, 3
2-input XOR	5

LOGIC CONFIGURATIONS



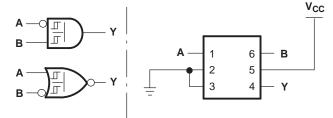
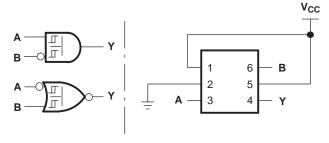


Figure 1. 2-Input NAND Gate

Figure 2. 2-Input AND Gate With Inverted A Input



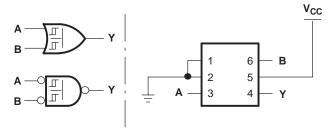


Figure 3. 2-Input AND Gate With Inverted B Input

Figure 4. 2-Input OR Gate

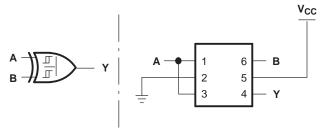


Figure 5. 2-Input XOR Gate



ABSOLUTE MAXIMUM RATINGS(1)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT	
V _{CC}	Supply voltage range		-0.5	4.6	V	
VI	Input voltage range ⁽²⁾	Input voltage range ⁽²⁾			V	
Vo	Voltage range applied to any output in the h	Voltage range applied to any output in the high-impedance or power-off state (2)			V	
Vo	Output voltage range in the high or low stat	e ⁽²⁾	-0.5	V _{CC} + 0.5	V	
I _{IK}	Input clamp current	V _I < 0		-50	mA	
lok	Output clamp current	V _O < 0		-50	mA	
Io	Continuous output current		±20	mA		
	Continuous current through V _{CC} or GND			±50	mA	
	3 33	DBV package		165		
		DCK package		259	42	
0	Declines the world inner dense (3)	DRL package		142		
θ_{JA}	Package thermal impedance (3)	DSF package		300	°C/W	
		DRY package		234		
		YFP/YZP package		123		
T _{stg}	Storage temperature range		-65	150	°C	

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS(1)

			MIN	MAX	UNIT	
V_{CC}	Supply voltage		0.8	3.6	V	
VI	Input voltage		0	3.6	V	
Vo	Output voltage		0	V_{CC}	V	
		V _{CC} = 0.8 V		-20	μΑ	
		V _{CC} = 1.1 V		-1.1		
	High-level output current	V _{CC} = 1.4 V		-1.7		
I _{OH}		V _{CC} = 1.65		-1.9	mA	
		V _{CC} = 2.3 V		-3.1		
		V _{CC} = 3 V		-4	ļ	
		V _{CC} = 0.8 V		20	μΑ	
		V _{CC} = 1.1 V		1.1		
	Low lovel output ourrent	V _{CC} = 1.4 V		1.7	mA	
I _{OL}	Low-level output current	V _{CC} = 1.65 V		1.9		
		V _{CC} = 2.3 V		3.1		
		V _{CC} = 3 V		4		
T _A	Operating free-air temperature		-40	85	°C	

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

Submit Documentation Feedback

²⁾ The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

⁽³⁾ The package thermal impedance is calculated in accordance with JESD 51-7.



ELECTRICAL CHARACTERISTICS

over recommended operating free-air temperature range (unless otherwise noted)

DADMETEE	TEOT OCCUPITIONS	.,	Т	_A = 25°C	T _A = -40°C	to 85°C	
PARMETER	TEST CONDITIONS	V _{cc}	MIN	TYP MAX	MIN	MAX	UNIT
V _{T+}		0.8 V	0.3	0.6	0.3	0.6	
		1.1 V	0.53	0.9	0.53	0.9	
Positive-going		1.4 V	0.74	1.11	0.74	1.11	.,
input threshold		1.65 V	0.91	1.29	0.91	1.29	V
voltage		2.3 V	1.37	1.77	1.37	1.77	
		3 V	1.88	2.29	1.88	2.29	
V _T		0.8 V	0.1	0.6	0.1	0.6	
		1.1 V	0.26	0.65	0.26	0.65	
Negative-going		1.4 V	0.39	0.75	0.39	0.75	
input threshold		1.65 V	0.47	0.84	0.47	0.84	V
voltage		2.3 V	0.69	1.04	0.69	1.04	
		3 V	0.88	1.24	0.88	1.24	
ΔV_{T}		0.8 V	0.07	0.5	0.07	0.5	
·		1.1 V	0.08	0.46	0.08	0.46	
		1.4 V	0.18	0.56	0.18	0.56	
Hysteresis		1.65 V	0.27	0.66	0.27	0.66	V
$(V_{T+} - V_{T-})$		2.3 V	0.53	0.92	0.53	0.92	
		3 V	0.79	1.31	0.79	1.31	
	I _{OH} = -20 μA	0.8 V to 3.6 V	V _{CC} - 0.1		V _{CC} - 0.1		
	I _{OH} = -1.1 mA	1.1 V	0.75 × V _{CC}		0.7 × V _{CC}		
	I _{OH} = -1.7 mA	1.4 V	1.11		1.03		
	$I_{OH} = -1.9 \text{ mA}$	1.65 V	1.32		1.3		
V_{OH}	I _{OH} = -2.3 mA		2.05		1.97		V
	I _{OH} = -3.1 mA	2.3 V	1.9		1.85		
	$I_{OH} = -2.7 \text{ mA}$		2.72		2.67		
	I _{OH} = -4 mA	3 V	2.6		2.55		
	I _{OL} = 20 μA	0.8 V to 3.6 V		0.1		0.1	
	I _{OL} = 1.1 mA	1.1 V		0.3 × V _{CC}		0.3 × V _{CC}	
	I _{OL} = 1.7 mA	1.4 V		0.31		0.37	
	I _{OL} = 1.9 mA	1.65 V		0.31		0.35	
V_{OL}	I _{OL} = 2.3 mA			0.31		0.33	V
	I _{OL} = 3.1 mA	2.3 V		0.44		0.45	
	I _{OL} = 2.7 mA			0.31		0.33	
	I _{OL} = 4 mA	3 V		0.44		0.45	
I _I All inputs	$V_I = GND \text{ to } 3.6 \text{ V}$	0 V to 3.6 V		0.1		0.5	μΑ
I _{off}	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V}$	0 V		0.2		0.6	<u>.</u> μΑ
ΔI_{off}	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V}$	0 V to 0.2 V		0.2		0.6	<u>.</u> μΑ
I _{cc}	$V_I = \text{GND or } (V_{CC} \text{ to } 3.6 \text{ V}),$ $I_O = 0$	0.8 V to 3.6 V		0.5		0.9	μА
ΔI _{CC}	$V_I = V_{CC} - 0.6 V^{(1)},$ $I_O = 0$	3.3 V		40		50	μА
C	V _I = V _{CC} or GND	0 V		1.5			pF
C _i	AI = ACC OI QIAD	3.6 V		1.5			þr.
C _o	V _O = GND	0 V		3			pF

⁽¹⁾ One input at V_{CC} – 0.6 V, other inputs at V_{CC} or GND.



SWITCHING CHARACTERISTICS

over recommended operating free-air temperature range, $C_L = 5 pF$ (unless otherwise noted) (see Figure 6 and Figure 7)

PARAMETER	FROM	то	V	T,	_A = 25°C	;	T _A = -40°C	to 85°C	UNIT	
PARAMETER	(INPUT)	(OUTPUT)	V _{cc}	MIN	TYP	MAX	MIN	MAX	UNII	
	In0, In1, or In2			0.8 V		23.6				
		Y	1.2 V ± 0.1 V	2.8	9.4	13.8	2.3	17.4		
			1.5 V ± 0.1 V	2.1	6.5	9.2	1.6	11.3		
t _{pd}			1.8 V ± 0.15 V	1.5	5.4	7.4	1	9	ns	
			2.5 V ± 0.2 V	1.1	4	5.6	0.6	6.6		
			3.3 V ± 0.3 V	1	3.2	4.6	0.5	5.5		

SWITCHING CHARACTERISTICS

over recommended operating free-air temperature range, C_L = 10 pF (unless otherwise noted) (see Figure 6 and Figure 7)

DADAMETED	FROM	то	V		4 = 25°C	;	T _A = -40°C	to 85°C	LINUT
PARAMETER	(INPUT)	(OUTPUT)	V _{cc}	MIN	TYP	MAX	MIN	MAX	UNIT
			0.8 V		26.4				
	In0, In1, or In2	Y	1.2 V ± 0.1 V	3.2	10.7	15.2	2.7	19	
			1.5 V ± 0.1 V	2	7.5	10.5	1.5	12.5	
t _{pd}			1.8 V ± 0.15 V	1.1	6.2	8.4	0.6	10.2	ns
			2.5 V ± 0.2 V	1	4.6	6.4	0.5	7.6	
			3.3 V ± 0.3 V	1	3.7	5.3	0.5	6.3	

SWITCHING CHARACTERISTICS

over recommended operating free-air temperature range, $C_L = 15 \text{ pF}$ (unless otherwise noted) (see Figure 6 and Figure 7)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC}	T _A = 25°C			$T_A = -40$ °C to 85°C		UNIT
FARAMETER				MIN	TYP	MAX	MIN	MAX	UNII
		Y	0.8 V		29.6				
	In0, In1, or In2		1.2 V ± 0.1 V	3.8	11.8	16.8	3.3	21.1	
			1.5 V ± 0.1 V	2.9	8.3	11.6	2.4	13.8	no
t _{pd}			1.8 V ± 0.15 V	2.2	6.8	9.3	1.7	11.3	ns
			2.5 V ± 0.2 V	1.7	5.1	7	1.2	8.4	
			3.3 V ± 0.3 V	1.4	4.2	5.9	0.9	7	

SWITCHING CHARACTERISTICS

over recommended operating free-air temperature range, $C_L = 30 \text{ pF}$ (unless otherwise noted) (see Figure 6 and Figure 7)

DADAMETER	FROM	то	V	T,	4 = 25°C	;	$T_A = -40^{\circ}C$ t	o 85°C	LINUT
PARAMETER	(INPUT)	(OUTPUT)	V _{cc}	MIN	TYP	MAX	MIN	MAX	UNIT
		0.8 V		38.1					
	In0, In1, or In2	Y	1.2 V ± 0.1 V	5.1	15	21.4	4.6	26.6	
4			1.5 V ± 0.1 V	4	10.6	14.6	3.5	17.4	
t _{pd}			1.8 V ± 0.15 V	3.2	8.7	11.7	2.7	14.2	ns
			2.5 V ± 0.2 V	2.5	6.5	8.7	2	10.5	
			3.3 V ± 0.3 V	2.1	5.4	7.3	1.6	8.7	

Product Folder Link(s): SN74AUP1G58

Submit Documentation Feedback



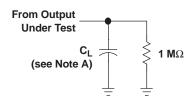
OPERATING CHARACTERISTICS

 $T_A = 25^{\circ}C$

	PARAMETER	TEST CONDITIONS	V _{cc}	TYP	UNIT
			0.8 V	4	
			1.2 V ± 0.1 V	4	pF
_	Dower discination conscitance	f 40 MHz	1.5 V ± 0.1 V	4	
C _{pd}	Power dissipation capacitance	f = 10 MHz	1.8 V ± 0.15 V	4	
			2.5 V ± 0.2 V	4.3	
			3.3 V ± 0.3 V	4.6	

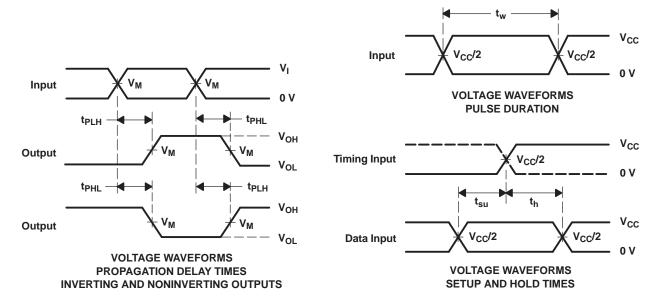


PARAMETER MEASUREMENT INFORMATION (Propagation Delays, Setup-and-Hold Times, and Pulse Duration)



LOAD CIRCUIT

	V _{CC} = 0.8 V	V _{CC} = 1.2 V ± 0.1 V	V _{CC} = 1.5 V ± 0.1 V	V _{CC} = 1.8 V ± 0.15 V	V_{CC} = 2.5 V \pm 0.2 V	V _{CC} = 3.3 V ± 0.3 V
C _L	5, 10, 15, 30 pF	5, 10, 15, 30 pF	5, 10, 15, 30 pF	5, 10, 15, 30 pF	5, 10, 15, 30 pF	5, 10, 15, 30 pF
V _M	V _{CC} /2	V _{CC} /2	V _{CC} /2	V _{CC} /2	V _{CC} /2	V _{CC} /2
V _I	V _{CC}	V _{CC}	V _{CC}	V _{CC}	V _{CC}	V _{CC}



NOTES: A. C_L includes probe and jig capacitance.

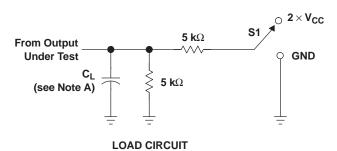
- B. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, slew rate \geq 1 V/ns.
- C. The outputs are measured one at a time, with one transition per measurement.
- D. t_{PLH} and t_{PHL} are the same as t_{pd} .
- E. All parameters and waveforms are not applicable to all devices.

Figure 6. Load Circuit and Voltage Waveforms

Submit Documentation Feedback

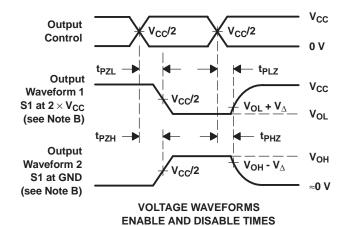


PARAMETER MEASUREMENT INFORMATION (Enable and Disable Times)



TEST	S1
t _{PLZ} /t _{PZL}	2×V _{CC}
t _{PHZ} /t _{PZH}	GND

	V _{CC} = 0.8 V	V _{CC} = 1.2 V ± 0.1 V	V _{CC} = 1.5 V ± 0.1 V	V _{CC} = 1.8 V ± 0.15 V	V _{CC} = 2.5 V ± 0.2 V	V _{CC} = 3.3 V ± 0.3 V
C _L	5, 10, 15, 30 pF	5, 10, 15, 30 pF	5, 10, 15, 30 pF	5, 10, 15, 30 pF	5, 10, 15, 30 pF	5, 10, 15, 30 pF
V _M	V _{CC} /2	V _{CC} /2	V _{CC} /2	V _{CC} /2	V _{CC} /2	V _{CC} /2
V _I	V _{CC}	V _{CC}	V _{CC}	V _{CC}	V _{CC}	V _{CC}
V _∆	0.1 V	0.1 V	0.1 V	0.15 V	0.15 V	0.3 V



NOTES: A. C_L includes probe and jig capacitance.

B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.

LOW- AND HIGH-LEVEL ENABLING

- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω , slew rate \geq 1 V/ns.
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
- F. t_{PZL} and t_{PZH} are the same as t_{en}.
- G. All parameters and waveforms are not applicable to all devices.

Figure 7. Load Circuit and Voltage Waveforms

Submit Documentation Feedback Copyright © 2003-2010, Texas Instruments Incorporated

www.ti.com 13-Jul-2022

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
SN74AUP1G58DBVR	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	H58R	Samples
SN74AUP1G58DBVT	ACTIVE	SOT-23	DBV	6	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	H58R	Samples
SN74AUP1G58DCKR	ACTIVE	SC70	DCK	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HJR	Samples
SN74AUP1G58DCKT	ACTIVE	SC70	DCK	6	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HJR	Samples
SN74AUP1G58DRLR	ACTIVE	SOT-5X3	DRL	6	4000	RoHS & Green	NIPDAU NIPDAUAG	Level-1-260C-UNLIM	-40 to 85	(1KD, HJ7, HJR)	Samples
SN74AUP1G58DRYR	ACTIVE	SON	DRY	6	5000	RoHS & Green	NIPDAU NIPDAUAG	Level-1-260C-UNLIM	-40 to 85	HJ	Samples
SN74AUP1G58DSFR	ACTIVE	SON	DSF	6	5000	RoHS & Green	NIPDAU NIPDAUAG	Level-1-260C-UNLIM	-40 to 85	HJ	Samples
SN74AUP1G58YFPR	ACTIVE	DSBGA	YFP	6	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM		HJN	Samples
SN74AUP1G58YZPR	ACTIVE	DSBGA	YZP	6	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	HJN	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.



PACKAGE OPTION ADDENDUM

www.ti.com 13-Jul-2022

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

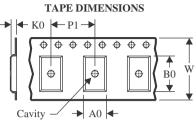
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.



www.ti.com 12-Feb-2023

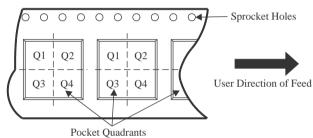
TAPE AND REEL INFORMATION





_	Tanana and a same and a same and a same and a same a s
A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

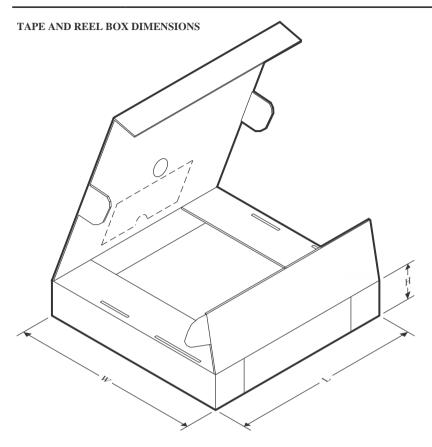


*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74AUP1G58DBVR	SOT-23	DBV	6	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74AUP1G58DBVT	SOT-23	DBV	6	250	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74AUP1G58DCKR	SC70	DCK	6	3000	180.0	8.4	2.41	2.41	1.2	4.0	8.0	Q3
SN74AUP1G58DCKT	SC70	DCK	6	250	180.0	8.4	2.41	2.41	1.2	4.0	8.0	Q3
SN74AUP1G58DRLR	SOT-5X3	DRL	6	4000	180.0	8.4	2.0	1.8	0.75	4.0	8.0	Q3
SN74AUP1G58DRLR	SOT-5X3	DRL	6	4000	180.0	8.4	1.98	1.78	0.69	4.0	8.0	Q3
SN74AUP1G58DRYR	SON	DRY	6	5000	180.0	9.5	1.15	1.6	0.75	4.0	8.0	Q1
SN74AUP1G58DSFR	SON	DSF	6	5000	180.0	9.5	1.16	1.16	0.5	4.0	8.0	Q2
SN74AUP1G58YFPR	DSBGA	YFP	6	3000	178.0	9.2	0.89	1.29	0.62	4.0	8.0	Q1
SN74AUP1G58YZPR	DSBGA	YZP	6	3000	178.0	9.2	1.02	1.52	0.63	4.0	8.0	Q1



www.ti.com 12-Feb-2023



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
					— `	, ,	
SN74AUP1G58DBVR	SOT-23	DBV	6	3000	202.0	201.0	28.0
SN74AUP1G58DBVT	SOT-23	DBV	6	250	202.0	201.0	28.0
SN74AUP1G58DCKR	SC70	DCK	6	3000	202.0	201.0	28.0
SN74AUP1G58DCKT	SC70	DCK	6	250	202.0	201.0	28.0
SN74AUP1G58DRLR	SOT-5X3	DRL	6	4000	210.0	185.0	35.0
SN74AUP1G58DRLR	SOT-5X3	DRL	6	4000	202.0	201.0	28.0
SN74AUP1G58DRYR	SON	DRY	6	5000	184.0	184.0	19.0
SN74AUP1G58DSFR	SON	DSF	6	5000	184.0	184.0	19.0
SN74AUP1G58YFPR	DSBGA	YFP	6	3000	220.0	220.0	35.0
SN74AUP1G58YZPR	DSBGA	YZP	6	3000	220.0	220.0	35.0



SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.25 per side.

- 4. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation. 5. Refernce JEDEC MO-178.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



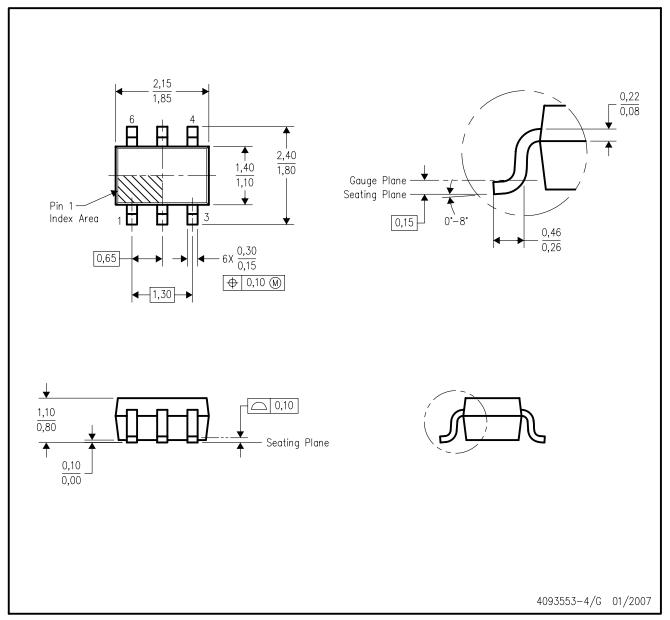
NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



DCK (R-PDSO-G6)

PLASTIC SMALL-OUTLINE PACKAGE



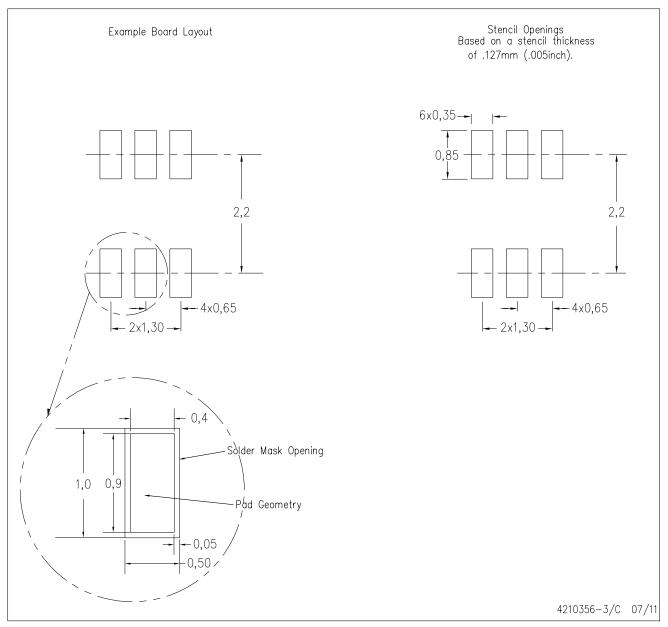
NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Falls within JEDEC MO-203 variation AB.



DCK (R-PDSO-G6)

PLASTIC SMALL OUTLINE

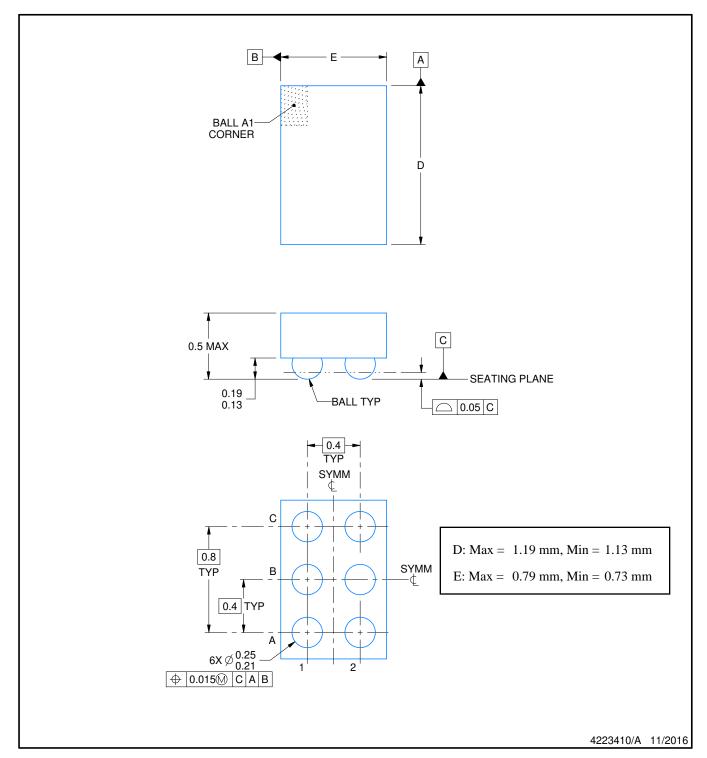


NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.



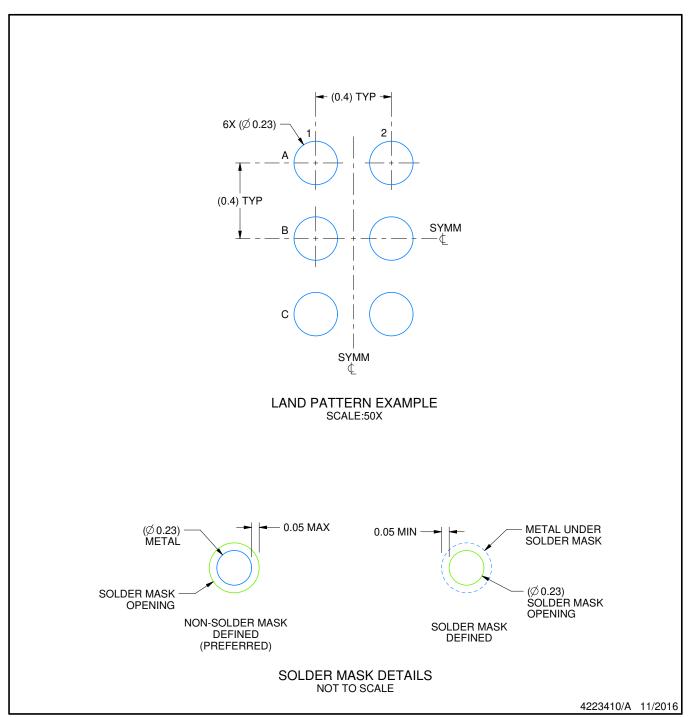




NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.

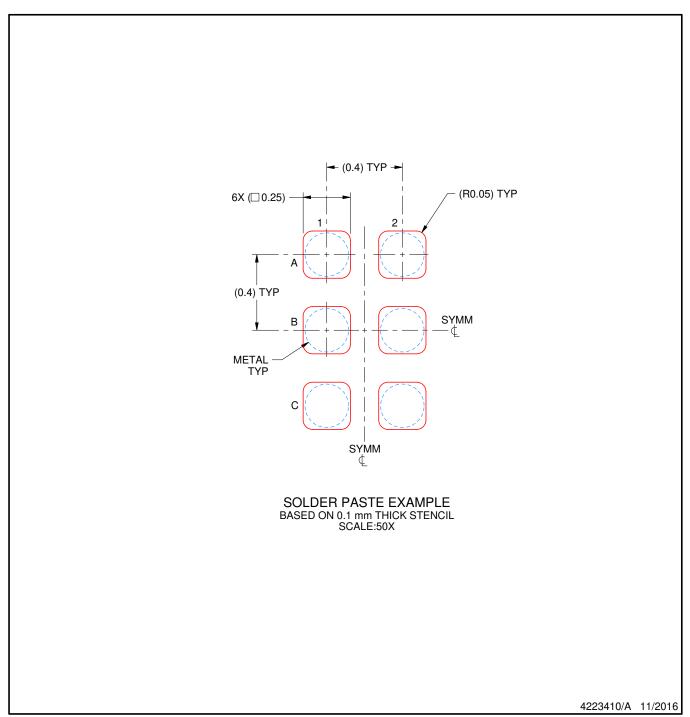




NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



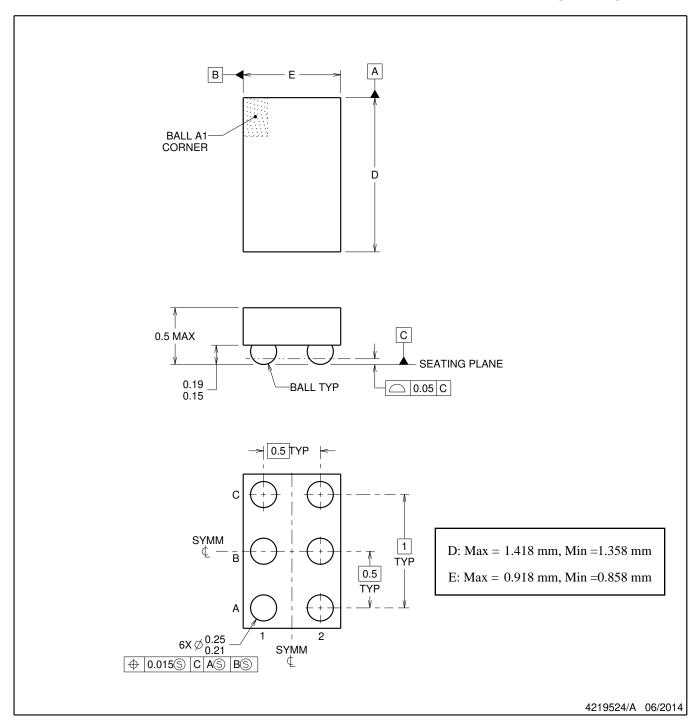


NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.







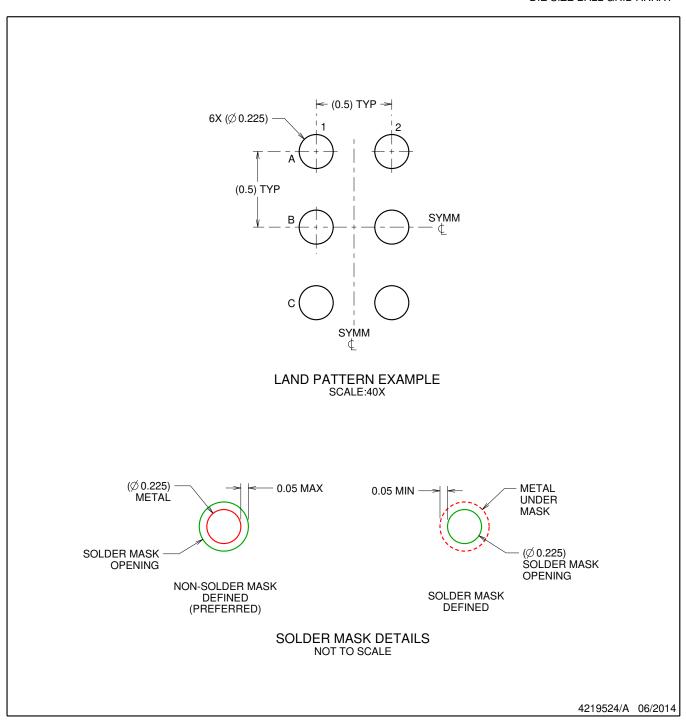
NOTES:

NanoFree Is a trademark of Texas Instruments.

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.
- 3. NanoFree[™] package configuration.

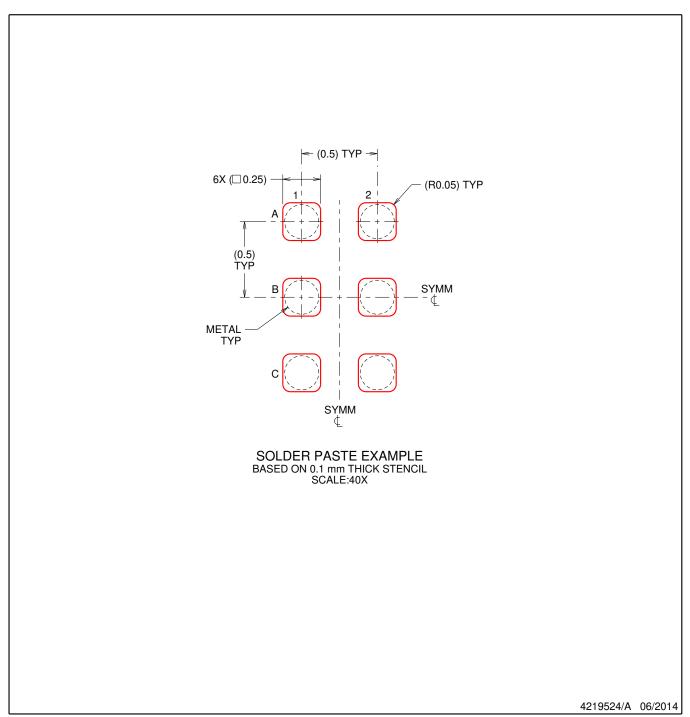




NOTES: (continued)

4. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SBVA017 (www.ti.com/lit/sbva017).





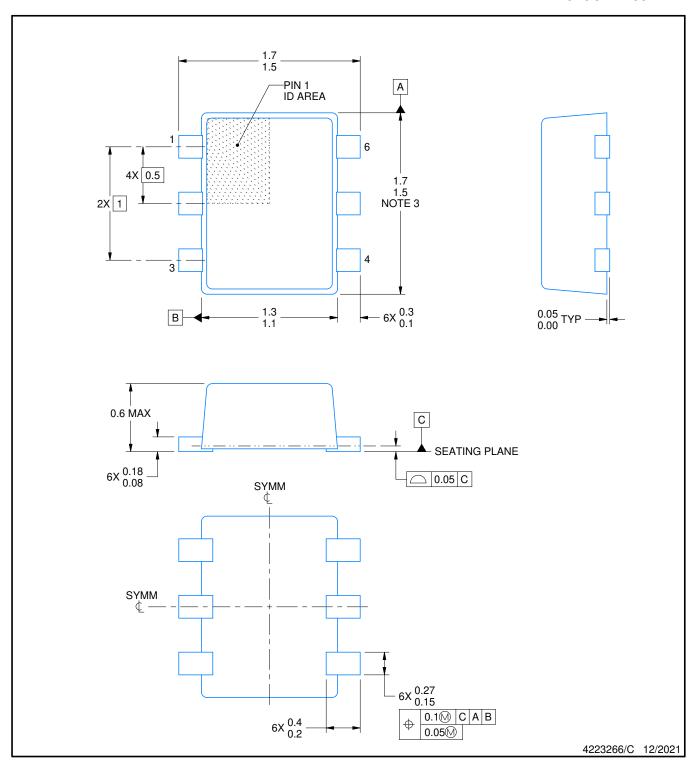
NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.





PLASTIC SMALL OUTLINE

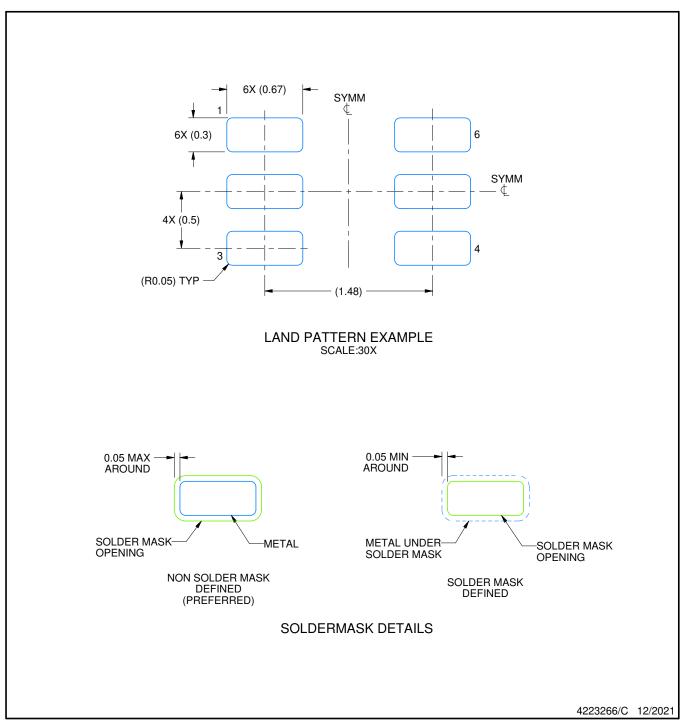


NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 This drawing is subject to change without notice.
 This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
 4. Reference JEDEC registration MO-293 Variation UAAD



PLASTIC SMALL OUTLINE



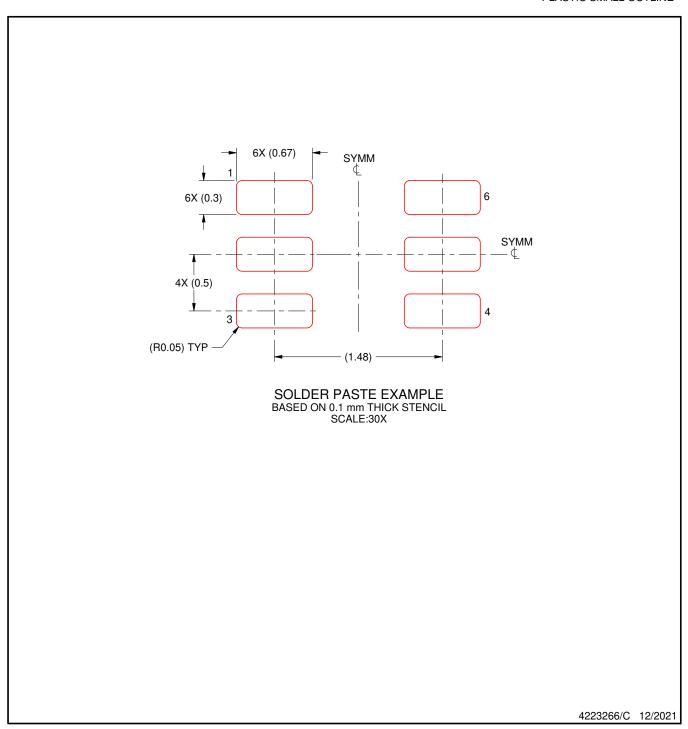
NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
7. Land pattern design aligns to IPC-610, Bottom Termination Component (BTC) solder joint inspection criteria.



PLASTIC SMALL OUTLINE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



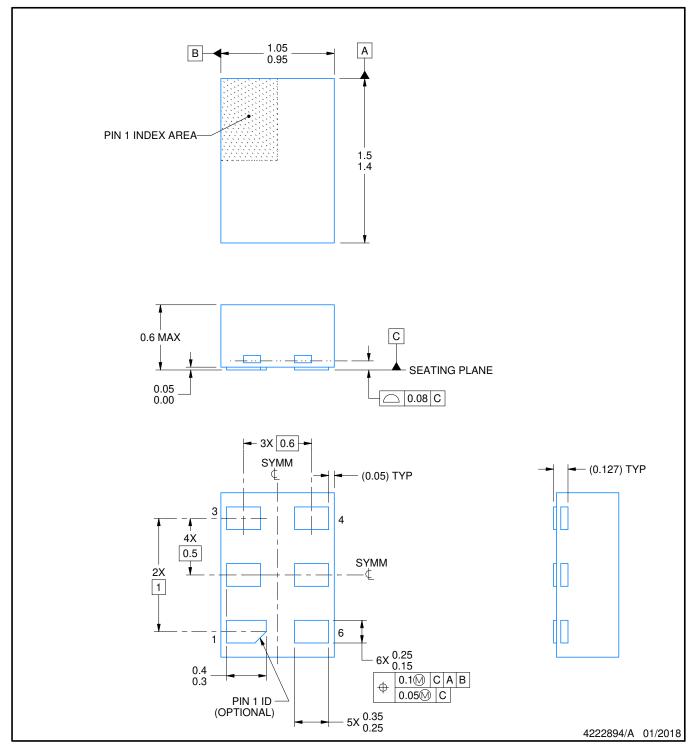


Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

4207181/G





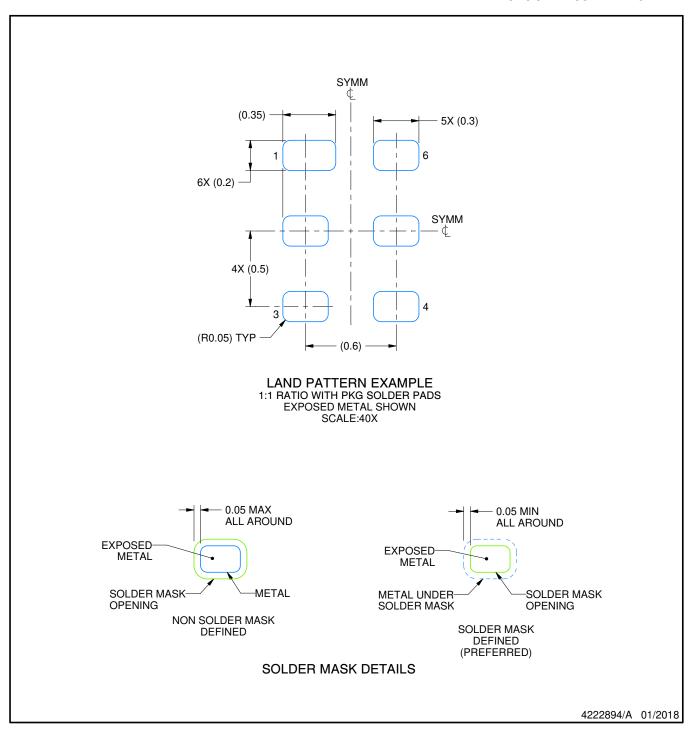


NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

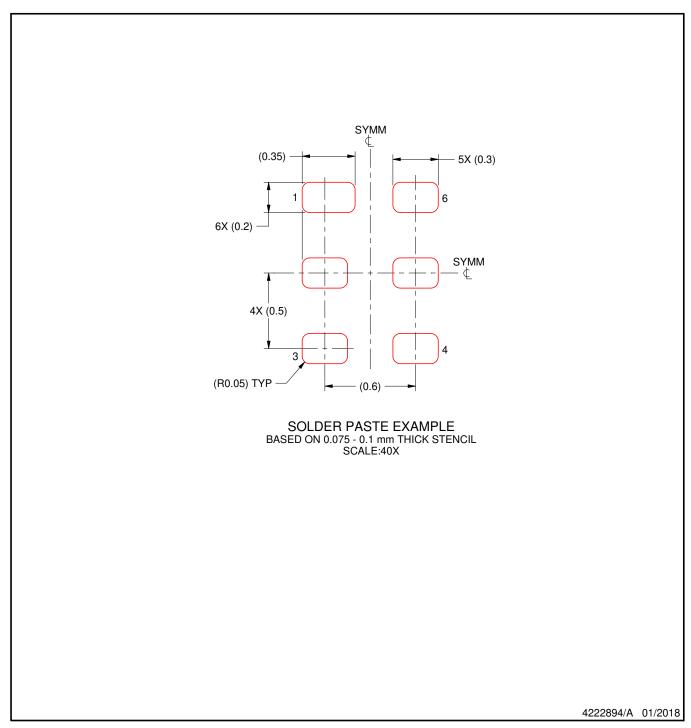




NOTES: (continued)

3. For more information, see QFN/SON PCB application report in literature No. SLUA271 (www.ti.com/lit/slua271).



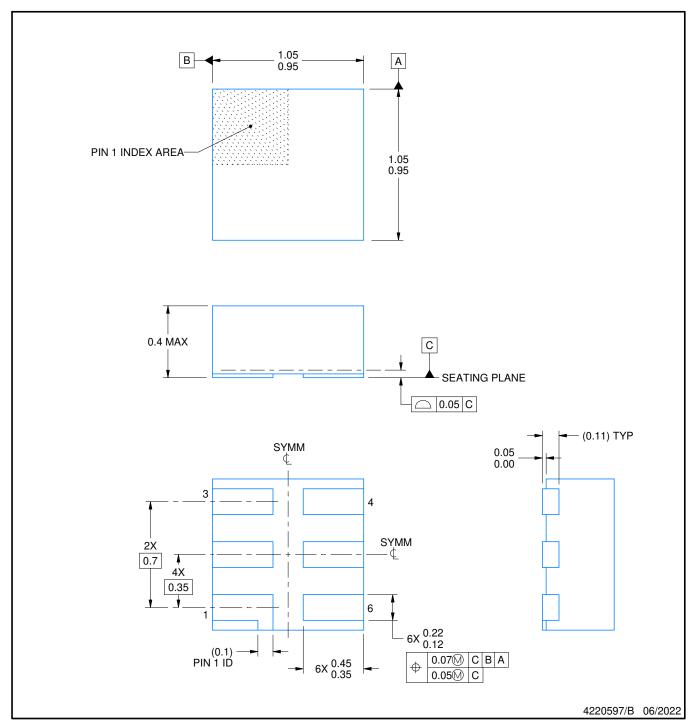


NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.







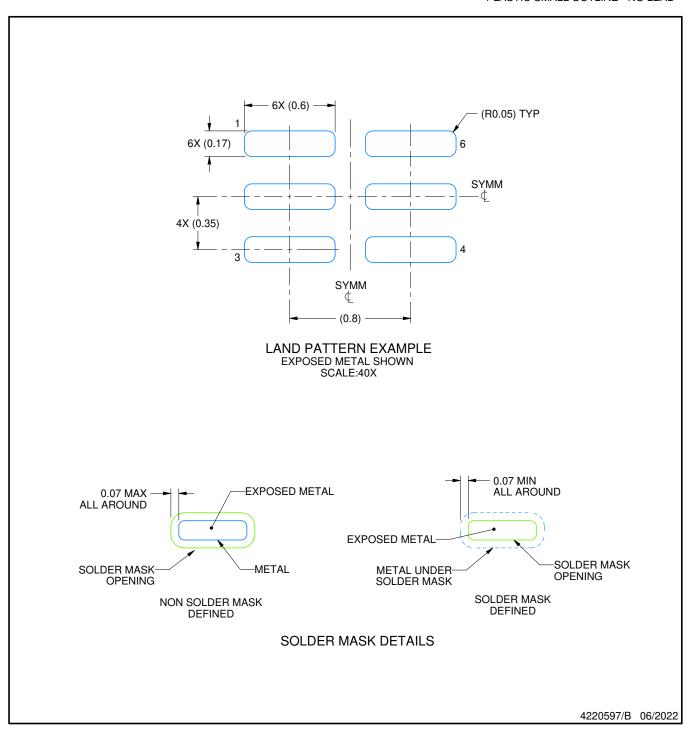
NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. Reference JEDEC registration MO-287, variation X2AAF.

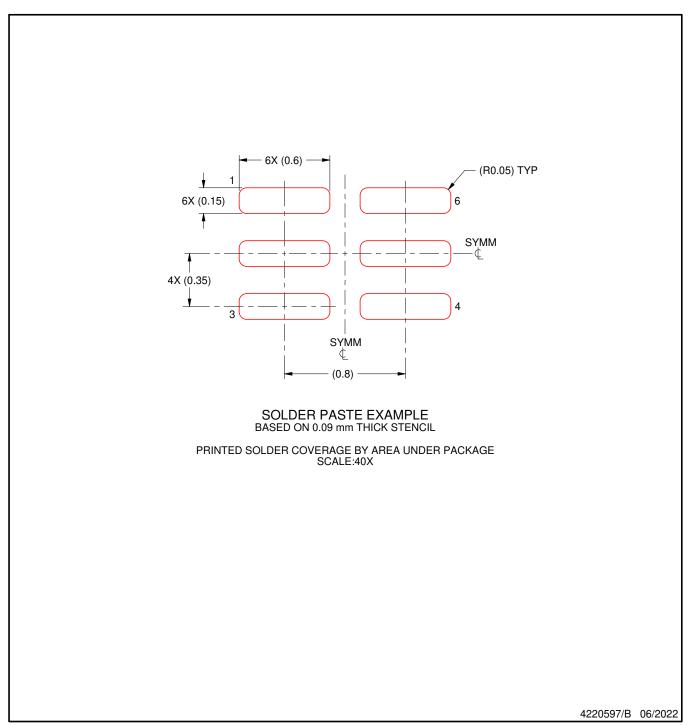




NOTES: (continued)

4. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).





4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2023, Texas Instruments Incorporated